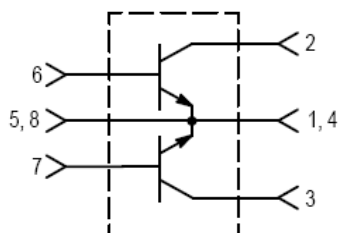


The RF Line Controlled "Q" Broadband Power Transistor 100W, 30 to 500MHz, 28V

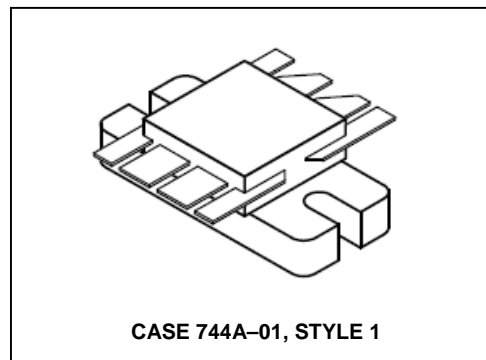
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Designed primarily for wideband large-signal output and driver amplifier stages in the 30 to 500 MHz frequency range.

- Specified 28 V, 500 MHz characteristics —
Output power = 100 W
Typical gain = 9.5 dB (Class AB); 8.5 dB (Class C)
Efficiency = 55% (typ.)
- Built-in input impedance matching networks for broadband operation
- Push-pull configuration reduces even numbered harmonics
- Gold metallization system for high reliability
- 100% tested for load mismatch



Product Image



The MRF393 is two transistors in a single package with separate base and collector leads and emitters common. This arrangement provides the designer with a space saving device capable of operation in a push-pull configuration.

PUSH-PULL TRANSISTORS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	16	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	270 1.54	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.65	$^\circ\text{C/W}$

NOTE:

- This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF push-pull amplifier.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS (1)

Collector–Emitter Breakdown Voltage (I _C = 50 mA _{dc} , I _B = 0)	V _{(BR)CEO}	30	—	—	V _{dc}
Collector–Emitter Breakdown Voltage (I _C = 50 mA _{dc} , V _{BE} = 0)	V _{(BR)CES}	60	—	—	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 5.0 mA _{dc} , I _C = 0)	V _{(BR)EBO}	4.0	—	—	V _{dc}
Collector Cutoff Current (V _{CB} = 30 V _{dc} , I _E = 0)	I _{CBO}	—	—	5.0	mA _{dc}

ON CHARACTERISTICS (1)

DC Current Gain (I _C = 1.0 A _{dc} , V _{CE} = 5.0 V _{dc})	h _{FE}	20	—	100	—
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DYNAMIC CHARACTERISTICS (1)

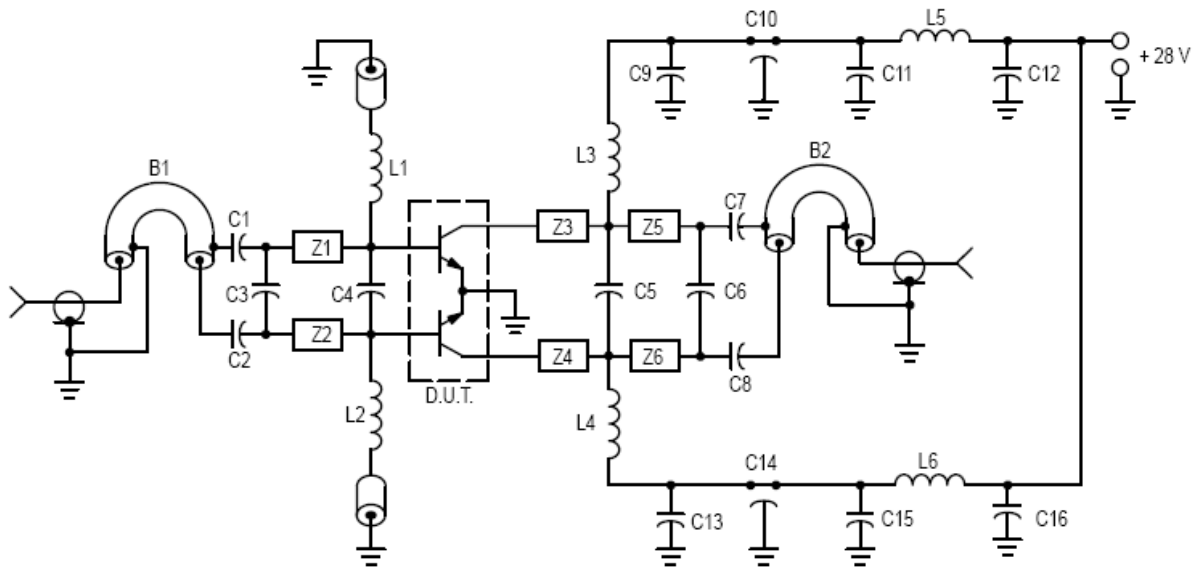
Output Capacitance (V _{CB} = 28 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{ob}	40	75	95	pF
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FUNCTIONAL TESTS (2) — See Figure 1

Common–Emitter Amplifier Power Gain (V _{CC} = 28 V _{dc} , P _{out} = 100 W, f = 500 MHz)	G _{pe}	7.5	8.5	—	dB
Collector Efficiency (V _{CC} = 28 V _{dc} , P _{out} = 100 W, f = 500 MHz)	η	50	55	—	%
Load Mismatch (V _{CC} = 28 V _{dc} , P _{out} = 100 W, f = 500 MHz, VSWR = 30:1, all phase angles)	ψ	No Degradation in Output Power			

NOTES:

1. Each transistor chip measured separately.
2. Both transistor chips operating in push–pull amplifier.



C1, C2, C7, C8 — 240 pF 100 mil Chip Cap
 C3 — 15 pF 100 mil Chip Cap
 C4 — 24 pF 100 mil Chip Cap
 C5 — 33 pF 100 mil Chip Cap
 C6 — 12 pF 100 mil Chip Cap
 C9, C13 — 1000 pF 100 mil Chip Cap
 C10, C14 — 680 pF Feedthru Cap
 C11, C15 — 0.1 μ F Ceramic Disc Cap
 C12, C16 — 50 μ F 50 V

L1, L2 — 0.15 μ H Molded Choke with Ferrite Bead
 L3, L4 — 2-1/2 Turns #20 AWG 0.200" ID
 L5, L6 — 3-1/2 Turns #18 AWG 0.200" ID
 B1, B2 — Balun 50 Ω Semi Rigid Coax, 86 mil OD, 4" Long
 Z1, Z2 — 850 mil Long x 125 mil W. Microstrip
 Z3, Z4 — 200 mil Long x 125 mil W. Microstrip
 Z5, Z6 — 800 mil Long x 125 mil W. Microstrip
 Board Material — 0.0325" Teflon-Fiberglass, $\epsilon_r = 2.56$,
 1 oz. Copper Clad both sides.

Figure 1. 500 MHz Test Fixture

CLASS C

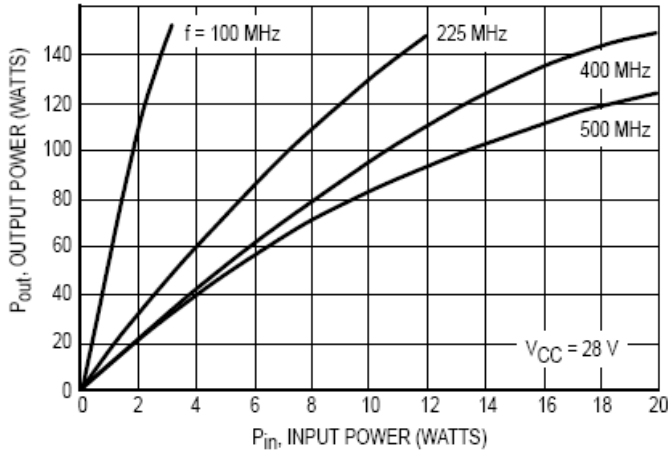


Figure 2. Output Power versus Input Power

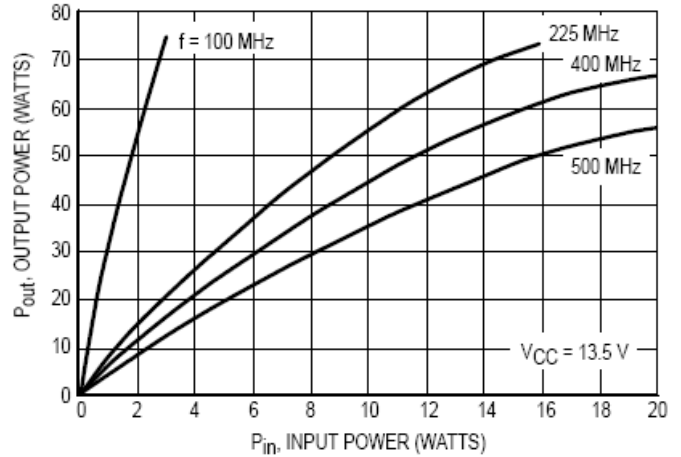


Figure 3. Output Power versus Input Power

CLASS C

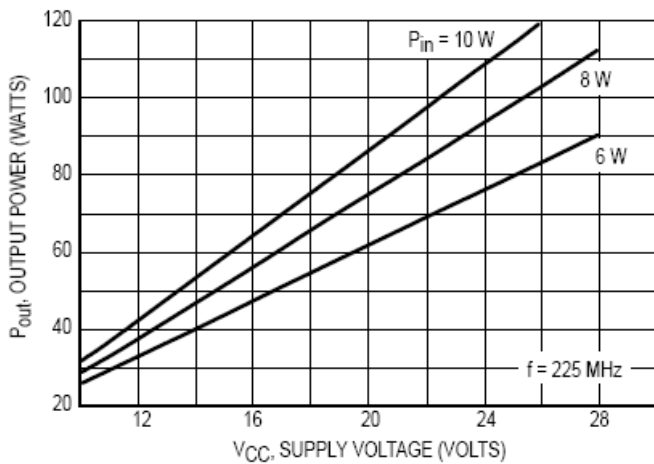


Figure 4. Output Power versus Supply Voltage

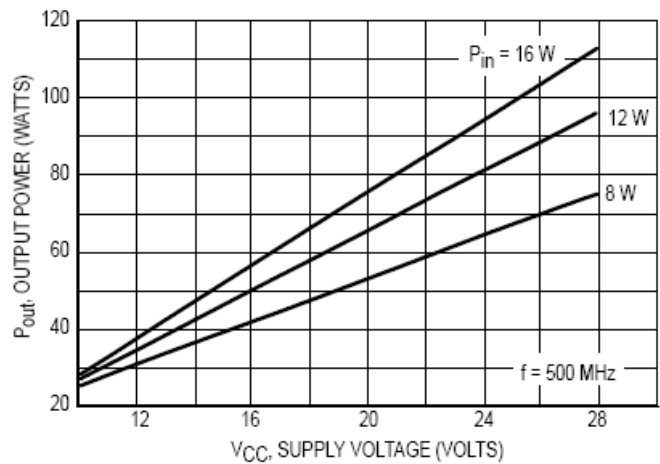
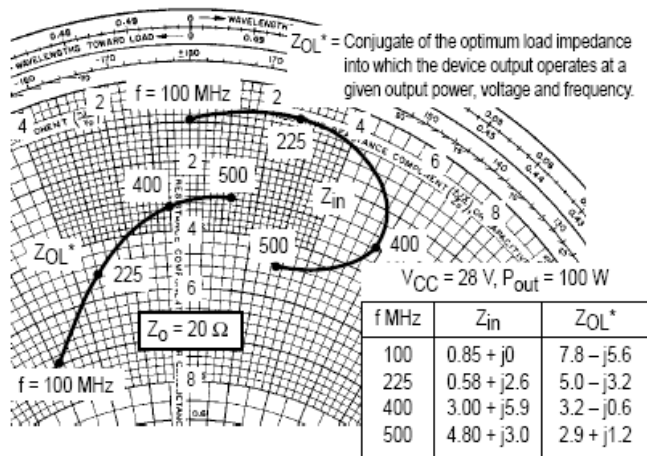


Figure 5. Output Power versus Supply Voltage

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NOTE: Z_{in} & Z_{OL}^* are given from base-to-base and collector-to-collector respectively.

Figure 6. Series Equivalent Input/Output Impedance

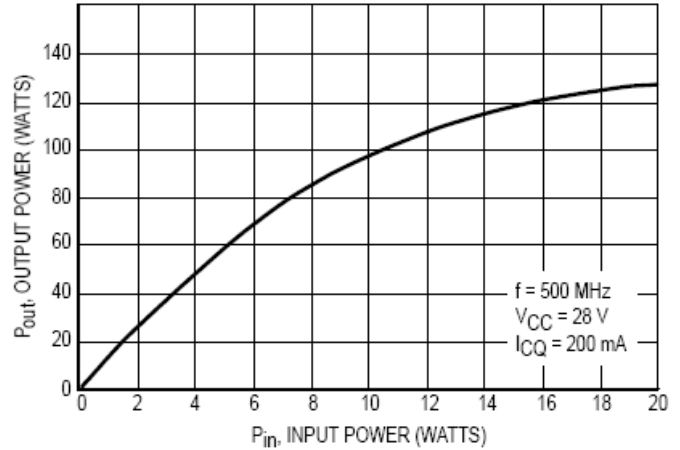


Figure 7. Class AB Output Power versus Input Power

PACKAGE DIMENSIONS

